

High-Efficiency L-band Transmit/Receive Module for Synthetic Aperture Radar

Wendy N. Edelstein, Constantine Andricos, Alina Moussessian
Jet Propulsion Laboratory
California Institute of Technology
4800 Oak Grove Drive
Pasadena, CA 91109-8099

Feiyu Wang, David B. Rutledge
Department of Electrical Engineering
California Institute of Technology
Pasadena, CA 91125

Abstract -- Space-based radar places significant demands on the spacecraft resources (mass, power, data rate) and is therefore very expensive to implement. These systems typically require active phased-array antennas with hundreds or thousands of Transmit/Receive (T/R) modules distributed on the array. High-efficiency is a vitally important figure of merit for the radar T/R module because it reduces the power consumption and therefore makes best possible use of the limited power available. High efficiency also improves the thermal design and reliability. In this paper, we describe the design and preliminary results of a novel L-band (1250 MHz) T/R module technology to achieve ultra-high efficiencies. We will show that a dramatic improvement in overall T/R module efficiency is possible using high-efficiency Class-E/F amplifiers. The T/R module performance goals are to achieve an overall module efficiency greater than 70% with a minimum of 30-Watts output power at L-band frequencies.

I. INTRODUCTION

Radar remote sensing plays an important role in deriving unique measurements that address fundamental questions in the National Aeronautic and Space Administration (NASA) Earth Science Enterprise (ESE) strategic plan [1]. Synthetic aperture radar (SAR) can provide measurements key to the water cycle (e.g. soil moisture and water level), global ecosystem (biomass estimation, land cover change), and ocean circulation and ice mass (ice motion). L-band radar provides the ability to make these measurements under a variety of topographic and land cover conditions, day or night, with wide coverage at fine resolution and with minimal temporal decorrelation [2, 3].

L-band repeat-pass interferometric SAR (InSAR) techniques can provide very accurate and systematic measurements of surface deformation and surface strain accumulation due to seismic and volcanic activity [4]. The dynamics of the solid Earth motion are complex and there are vigorous efforts to model, understand and eventually predict earthquakes using InSAR data. L-band InSAR is also useful for natural hazard monitoring, assessment and disaster response.

L-band SAR technologies developed for NASA also have national-security application. For example, these techniques could provide observations that are complementary to the traditional high resolution imagery of the intelligence community. L-band SAR can provide information on vehicle and troop movements, and building damage. Significant contributions are also possible in providing detailed surface characteristics, such as the measurement of surface soil moisture and sub-pixel roughness for trafficability, which could have dual-use science and military application. Furthermore, L-band radar technologies could also have application to future DoD space-based radar (SBR) for airborne moving target indication (AMTI) and ground moving target indication (GMTI).

A. System Requirements

Large, lightweight, high power, electronically-steerable L-band phased-arrays are required to enable the next-generation NASA Earth science SAR missions. L-band is the preferred frequency for land-related studies because the wavelength favors long-term correlation, is less sensitive to ionospheric disturbances and has sufficient frequency allocated bandwidth. Electronically-steered phased array antennas are required for beam agility to enable rapid accessibility, global coverage and short revisit times.

Future NASA L-band SAR missions, such as concepts currently being studied from LEO to geosynchronous orbits, require very powerful radar systems [5, 6]. For these systems, dramatic improvements in overall efficiency will help make near-term missions with moderate transmit power requirements (2-10KW) more reliable and affordable and could enable next-generation missions at MEO or geosynchronous orbits which have much higher transmit power requirements (>20KW). In the most advanced applications, very high efficiency is paramount.

The T/R module is a key component in electronically-steered antennas (ESA) and the T/R module efficiency has direct implications on the power dissipation and power generation requirements of the system. Significant improvements in the efficiency of the T/R module will make very large, high power, two-dimensionally scanned radar antennas more feasible and affordable. By miniaturizing the high-efficiency T/R modules, they can be used for both conventional rigid panel phased-array antennas as well as in more advanced super lightweight flexible membrane antennas currently being developed for future NASA missions [7]. Significant improvements in efficiency will also simplify the thermal design and increase reliability, particularly for membrane antennas, where heat dissipation is particularly challenging.

B. Technical Challenges

We are developing high-efficiency L-band T/R modules for use in future NASA radar missions. At the heart of the new T/R module architecture is a Class-E/F switching amplifier used as the power amplifier (PA). The potential of switching power amplifiers has been known for many years [8], however most of the research has been limited to the RF frequencies below 500 MHz. A 50 MHz high-efficiency (93%) high power (30W) Class-E power amplifier [9] and a 144MHz Class-E amplifier with 54W output power and 70% efficiency [10] were recently reported. In this paper we discuss the use of a new Class-E/F power amplifier at L-band frequencies. The design goals are to achieve 30 Watts at L-band (1.25 GHz) with greater than 80 MHz bandwidth and over 80% drain efficiency. By integrating the Class-E/F power amplifier into an L-band T/R module, overall T/R module efficiencies on the order of 70% can be achieved. Current T/R modules can only achieve moderate efficiencies of 30-40%. The highly efficient T/R module also helps address the challenges of power consumption, thermal dissipation, temperature control, and reliability common for space-based active antennas.

II. CLASS-E/F POWER AMPLIFIERS

Switching amplifiers, such as Class-E and Class-E/F amplifiers, use the active devices as switches. That is, the active device is ideally fully-on (short-circuit) or fully-off (open-circuit). These circuits are commonly found in switching power supplies, but only recently have they been exploited as RF amplifiers due to the availability of transistors with substantial gain and power at microwave frequencies. The theoretical efficiency for Class-E and Class-E/F amplifiers is 100%; practical efficiencies of 70-90% have been demonstrated at VHF and UHF frequencies [8, 9, 10].

A. Switching-Mode Power Amplifiers

In switching-mode amplifiers, the transition between the on-state and the off-state can be achieved instantaneously. The

switching-mode amplifiers differ from the traditional classes of amplifiers, which use the active devices as controlled current sources. Since ideally the device is either fully-on or fully-off, the voltage and the current will never be non-zero simultaneously. Therefore, ideally no power is dissipated, and the efficiency is 100%. This theoretical number is much higher than the traditional amplifiers, such as Class-A, Class-B and Class-C amplifiers. To achieve ultra-high efficiency, there are four primary loss mechanisms to overcome: conduction loss, input power loss, discharge loss, and passive component loss. The first three loss mechanisms are due to the active devices. Active device losses for switch-mode amplifiers occur mainly during transitions from one switch state to another. By using a high-Q resonant output network, Class-E and Class-E/F amplifiers minimize this switching loss. At L-band, the active devices are typically large in size, have large on-resistance, large output capacitance, and very low input impedance; all contributing to the loss. The last loss mechanism is due to the passive networks. The design of a low loss passive network also presents technical challenges. Due to the topology of the push-pull amplifier, a balun is used to convert the single-ended signal to a double-ended signal at the input and vice versa at the output. This balun must be small and planar with a flexible geometry for easy integration into the amplifier circuit. Proper modeling of parasitic capacitance and inductance is also another important challenge to ensure the circuit can be properly designed and reproduced to the given requirements.

B. Push-Pull Class-E/F power amplifiers

In his recent work, S. Kee has reported a new class of power amplifiers – the Class-E/F amplifier [11]. Fig. 1 shows the schematic of a Class-E/F amplifier in push-pull configuration. The amplifier uses a pair of transistors as switches. The transistors are driven at 180-degrees out of phase. The tuning circuit includes a parallel LC circuit with the output capacitance of the transistor. The tuning circuit is slightly inductive to minimize the discharging loss of the capacitance.

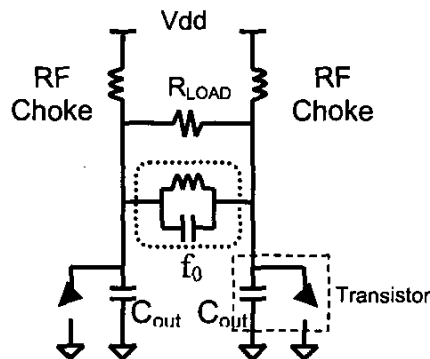


Fig. 1. Schematic of Push-Pull Class-E/F Power Amplifier

The push-pull Class-E/F amplifier has several advantages. It combines two transistors to achieve higher power level. It incorporates the transistor output capacitance into the tuning circuit. Since most high power devices have high output capacitance, this feature improves the performance of the tuning circuit and allows high operating frequency. By symmetry of the push-pull configuration, the amplifier suppresses the even harmonics of the operating frequency, thereby achieving higher efficiency. In comparison with Class-E amplifiers, it has lower peak voltage. It also has lower RMS current, which reduces resistive loss of the circuit. It has soft-switching, which keeps the current at a low level while the capacitors discharge. This feature reduces the discharging loss of the amplifier. Compared to the Class-E amplifier, the Class-E/F amplifier also has a less complex circuit and can potentially be used for higher frequency and bandwidth applications.

C. Low loss L-band microstrip balun

Due to the topology of push-pull amplifiers, a balun is required at the input and output of the amplifier to convert the single-ended signal to double-ended. There are many different varieties of microwave baluns. However, at L-band, the traditional microwave baluns are not practical due to the large size. A microstrip balun has been reported [12] that uses two small sections of magnetically coupled metals as the balun. This balun is smaller than the conventional microwave balun. It is planar, and it has a flexible geometry. However, the drawback of the balun is the low coupling coefficient between the primary and the secondary inductors. Previously reported work uses two microstrip inductors side-by-side (Fig. 2). Better coupling can be achieved using interdigital coupled inductors (Fig. 3). Using this method, the magnetic field is more confined inside the structure, which increases the magnetic coupling between the primary and the secondary inductors.

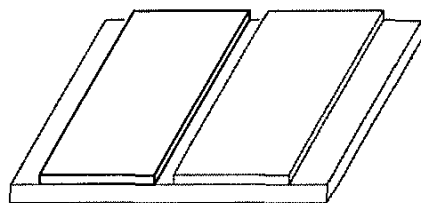


Fig. 2. Coupled inductors.

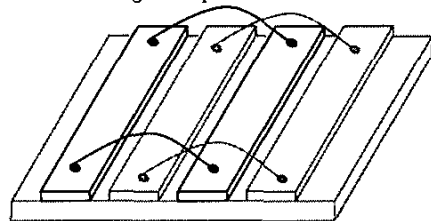


Fig. 3. Interdigital coupled inductors.

III. L-BAND HIGH EFFICIENCY T/R MODULE

To investigate the utility of Class-E/F amplifiers in a radar system application, a complete L-band T/R module is being designed and built. A key component in the module is the 30W high-efficiency Class-E/F power amplifier. The goal is to achieve the highest possible efficiency in both the transmit and receive modes since low average power consumption is a critical factor in space applications. The module contains a complete 30W transmitter, a low noise amplifier and a common 6-bit programmable attenuator and phase shifter. The performance goals for the final integrated T/R module are given in Table I.

TABLE I
PERFORMANCE GOALS OF THE INTEGRATED T/R MODULE

Parameter	Value
Frequency	1250 MHz
Bandwidth	80 MHz
Peak Transmit Power	30 Watts
Overall Module Efficiency	70%
Pulsewidth	50 μ sec
PRF	2000 Hz
Transmit Gain	48 dB
Receive Gain	25 dB
Receive Noise Figure	< 2.5 dB
Phase Shifter	6-bit
Rx Third Order Intercept (output)	> +5 dBm
Tx/Rx Programmable Attenuator	30 dB in 0.5 dB steps
VSWR	<1.5:1
T/R Module Mass	<100 g
T/R Module Size	2.5in x 1.5in x 0.25in

A. Design Requirements

The key parameters in the transmitter design are 30-Watts peak output power with a minimum transmit efficiency of 73% operating at 1.25 GHz over 80 MHz bandwidth. In the receiver chain, the goals are 25 dB of gain, less than 2.5 dB noise figure, with output 3rd order intercept point of +5 dBm, and less than 100 mW of DC power. The total T/R module calculated DC power drawn with 10% duty cycle is 4.2 watts which corresponds to 67% overall module efficiency. This includes the receiver low noise amplifiers, attenuator, phase shifter and switches. We believe that with improvements in other components of the module (i.e. receiver, driver amplifier and circulator), an overall efficiency of 70% is achievable.

B. Architecture

The block diagram of the T/R module, given in Fig. 4, shows all of the elements of the transmitter, receiver and the control and power switches. A common 6-bit phase shifter and programmable attenuator are used for both receive and transmit chains. The RF circuits use GaAs MMICs except for the high-efficiency power amplifier which currently uses silicon LD-MOS technology.

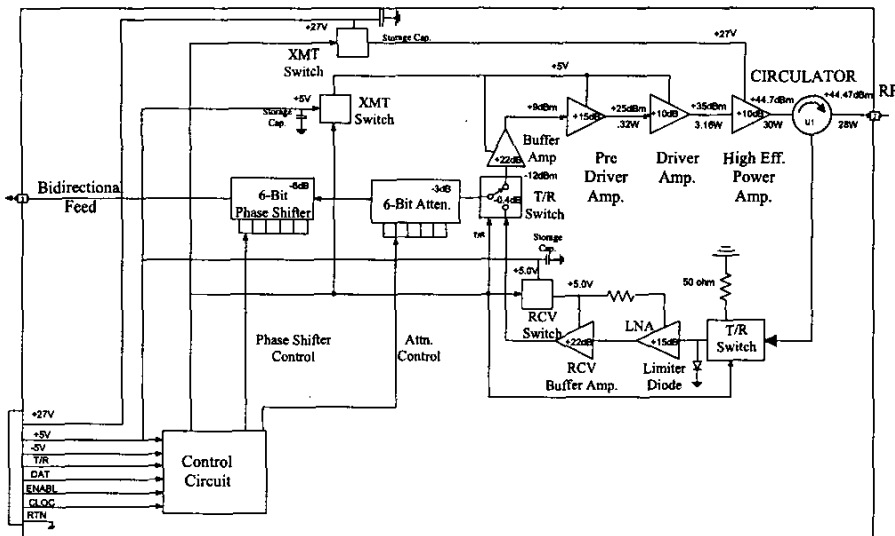


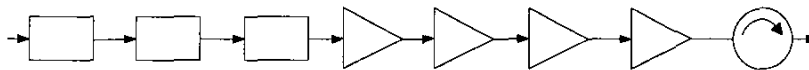
Fig. 4. L-band T/R Module block diagram. The 30W Class-E/F power amplifier is the final power amplifier.

Transmit Chain

The transmit chain consists of a buffer amplifier, a pre-driver amplifier, a medium power driver amplifier, and the high-efficiency Class-E/F amplifier. The circulator provides isolation for the receiver, as well as VSWR protection for the power amplifier. The details of the transmit chain analysis are given in Table II. The table shows the gain, power in, power out, and drain efficiency of each element of the transmitter. Also given at each stage are the 1 dB compression point, the operating voltage and current and power dissipated. We project that the power amplifier will attain 85% efficiency with 10dB gain and 30 watts of output power. This amplifier operates in Class-E/F

mode, as previously described, utilizing Motorola MRF284 MOSFET devices in a push-pull configuration. For high-efficiency these devices are driven above the 1 dB compression point. The medium power driver amplifier is a GaAs HJ-FET operating at +5V and producing +34.7 dBm of power with 60% drain efficiency and 10 dB of gain. For optimum efficiency this FET is also driven in compression. The pre-driver and buffer amplifier combined provide 37 dB of gain with lower efficiencies. The input RF power to the T/R module is -2.8 dBm. The total transmit efficiency is 73%. Additional losses in the module due to the power MOSFET switches and the control circuits are negligible in the transmit mode.

TABLE II
TRANSMIT CHAIN ANALYSIS



	Unit	Phase shifter	Attenuator	T/R switch	Buffer amp.	Pre-driver	Driver amp.	Power amp.	circulator	Total
Gain	dB	-6	-3	-0.4	22	15	10	10	-0.3	47.3
Power in	dBm	-2.83	-8.83	-11.83	-12.23	9.77	24.77	34.77	44.77	
Power out	dBm	-8.83	-11.83	-12.23	9.77	24.77	34.77	44.77	44.47	
Power out	W	-	-	-	0.0095	0.3	3	30	28	
1dB compression	dBm	20	20	20	12	24	34	45	-	
Drain efficiency	%	-	-	-	10	45	60	85	-	
Voltage	V	-	-	-	5	5	5	27	-	
Current	A	-	-	-	0.019	0.13	1	1.31	-	
DC power	W	-	-	-	0.095	0.65	5	35.3	-	41.05
Power dissipated	W	-	-	-	0.085	0.36	2.3	8.3	2	
Transmit eff. w/o circ.	%	73								
Transmit eff. w/ circ.	%	68								
Total avg. DC power	W	4.2								
Overall module eff.	%	66.6								

(This assumes 10% duty cycle and a DC power of less than 100mW for the receiver)

Receive Chain

The receive channel consists of the high power T/R switch, the LNA, and the receive buffer amplifier. The T/R switch in combination with the circulator provides receive protection during the 30-Watt transmit cycle. The high power T/R switch gives 35 dB of isolation so that with a worst case 5 dB return loss at the antenna port, 40 dBm or 10 Watts flowing into the receiver would be attenuated to + 5 dBm into the LNA. A limiter diode at the input to the LNA provides additional protection of input signals up to +15 dBm for transmit leakage and jamming signals while in the receive mode. The LNA has 1.5 dB of noise figure 15 dB of gain and draws less than 5 mA at 3 V. The receive buffer amplifier has an additional 22 dB of gain and draws 14 mA. The total receive channel has a noise figure of 2.5 dB and 26 dB of gain. The third order output intercept point is + 5 dBm at maximum gain. The circulator and T/R switch combined losses are about 1 dB.

Attenuator and Phase shifter

The programmable attenuator and phase shifter will be used to set the insertion gain and phase of each T/R element to steer the beam and control the sidelobe levels. The common channel contains the low loss GaAs switch, the 6-bit programmable attenuator and the phase shifter. At minimum attenuation setting the combination has about 9.5 dB of loss. Both devices use GaAs-FET switches as control elements to maintain high intercept point operation. The phase shifter has less than 3-degrees RMS error over all bits with less than 1 dB gain variation. The attenuator has a maximum of 31.5 dB attenuation with 0.5 dB resolution, and 0.5 dB total accuracy.

Control/power

The control circuit interfaces the module with the external commands, setting the 6-bits of the attenuator and phase shifter and controls the T/R switches. It also provides commands to the T/R MOSFET switches to activate the drain voltages of each channel alternately. The input data is serial and clocked in to the control circuits and stored during each update cycle. Well regulated power supplies of +27 V, + 5 V and - 5 V with low ripple and noise content are inputs to the module, where they are additionally filtered. Storage capacitors supply the peak turn-on currents to the power amplifier stages and maintain the drain voltages with small droop.

C. Implementation

A preliminary layout of the T/R module is shown in Fig. 5. The circuits will be integrated on one multi-layer circuit board to achieve a compact T/R module package. The overall module size is estimated at 2.5in x 1.5in x 0.25in and the weight is 100 grams. All the components are surface mount devices and will be eutectically attached to the printed

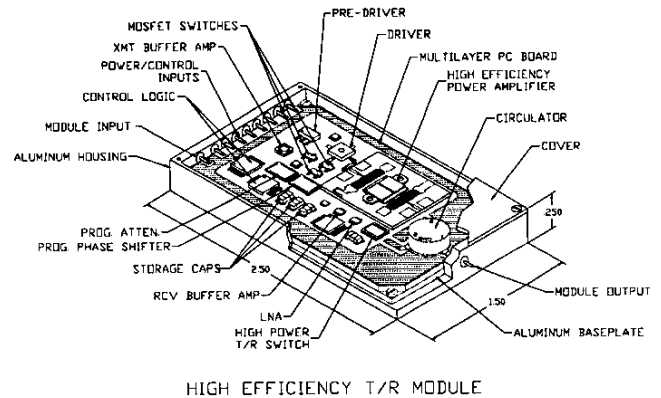


Fig. 5. Preliminary layout of integrated T/R module.

circuit board except for the power amplifiers and the circulator. These will be soldered directly to the plated aluminum baseplate for good grounding and heat sinking. A matching network between the driver and the high power amplifier will be incorporated to optimize the VSWR and efficiency.

IV. RESULTS

The efforts described in this paper are part of a three-year on-going task sponsored by the NASA Earth Science Technology Office (ESTO) under the Advanced Component Technology (ACT) program. The results reported here are the results of the first phase of the program to establish overall feasibility of using Class-E/F amplifiers at microwave frequencies and to establish their utility as an integral element of an innovative new T/R module architecture that can achieve very high radar instrument operating efficiencies.

Fig. 6 shows a picture of the Class-E/F power amplifier. The output power and drain efficiency are measured and shown in Fig. 7. The measurement was performed at 800 MHz. At 30 W output power level, 12 dB gain and 64% drain efficiency is achieved. The current operating frequency is less than the target 1215-1300 GHz, which may be due to the parasitic capacitances and inductances. Further improvements need to be made to adjust the operating frequency.

In parallel with the Class-E/F PA development, a breadboard T/R module was built using commercially available components (Fig. 8). The performance of the complete T/R module will be characterized before proceeding to the next phase.

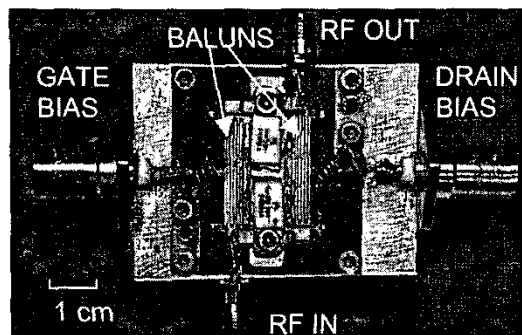


Fig. 6. Picture of L-Band Class E/F PA

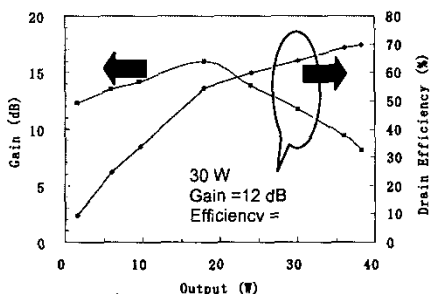


Fig. 7. Output power, efficiency and gain of the PA at 800 MHz

V. FUTURE WORK

Improvements to the power amplifier operation and performance are being addressed. Currently the amplifier works at 800 MHz, which differs from the target frequency of operation. The first step is to adjust the center frequency of the amplifier to 1.25 GHz. To improve the efficiency of the amplifier, harmonic traps will be added at the output to reduce the harmonics of the fundamental frequency. Once we optimize the performance of the PA and address interface issues, the entire T/R module will be integrated on one multilayer circuit board for a compact T/R module package.

A study is planned to compare different device technologies. GaAs FET devices are a possible alternative. Also wide bandgap devices, such as SiC and GaN transistors, have shown promise in high-frequency and high-power applications. The comparison between LDMOS, GaAs, SiC and GaN, will be a part of future studies.

VI. SUMMARY

A Class-E/F power amplifier based on LD-MOS transistors operating at 800 MHz was demonstrated experimentally. The 30-Watt amplifier achieved 64% efficiency. Efforts are underway to increase the operating frequency to L-band (1250 MHz) and improve the efficiency by improving the novel balun circuit. A complete L-band T/R module has been designed,

simulated and prototyped which incorporates the Class-E/F amplifier. Performance predictions indicate a 67% overall module efficiency.

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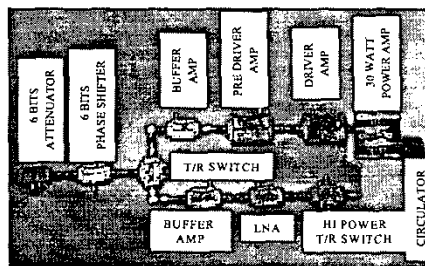


Fig. 8. Breadboard of complete L-band T/R module.